

15. MISCELLANOUS TRANSISTORS

IN ORDER OF: (1)CATEGORY,(2)TYPE NO.

| LINE No. | TYPE No. | U S E | CATEGORY S T R U C T U R E | M A T | DWG # Y 2 0 0 S/ a T O 2 0 0 S e | L C E O A D E | DESCRIPTION |
|----------|-------------|-------------|-------------------------------------------------------|-------------|-------------------------------------------------------------------------|---------------------------------|-------------------------------------------------------------------------------------|
| 1 | 2N3033 | 1 | N | Si | TO18 | A | P-300mW;BVCEO:160V max;IC:10A peak;tr:2nsec max;td:3nsec max. |
| 2 | 2N3034 | 1 | N | Si | TO18 | A | P-300mW;BVCEO:120V max;IC:10A peak;tr:2nsec max;td:3nsec max. |
| 3 | 2N3035 | 1 | N | Si | TO18 | A | P-300mW;BVCEO:90V max;IC:10A peak;tr:2nsec max;td:3nsec max. |
| 4 | 2N5271† | 1 | N | Si | TO39 | A | P-600mW;BVCEO:280V max;ICER 20nA max;ICER(H) 500μA min;VO 100V min. |
| 5 | CK273 | 1 | N | Si | TO5 | A | P-25W max; BVCEO:25V. |
| 6 | CK277 | 1 | N | Si | TO5 | A | P-25W max; BVCEO:90V. |
| 7 | 2N592 | 2 | P-A | Ge | TO5 | A | Pt 125mW;BVCEO 20V;ICBO 5.0uA,hfe 40typ;Cob 35p typ;NF 16db;fab 400k min |
| 8 | 2N593 | 2 | P-A | Ge | TO5 | A | Pt 125mW;BVCEO 40V;ICBO 5.0uA,hfe 80typ;Cob 35p typ;NF 16db;fab 600k min |
| 9 | 2N594 | 2 | N-A | Ge | TO5 | A | Pt 100mW;BVCEO 20V;ICBO 5.0uA,hfe 30typ;Cob 15p typ;NF 16db;fab 1.5M min |
| 10 | 2N595 | 2 | N-A | Ge | TO5 | A | Pt 100mW;BVCEO 15V;ICBO 5.0uA,hfe 45typ;Cob 15p typ;NF 16db;fab 3.0M min |
| 11 | 2N596 | 2 | N-A | Ge | TO5 | A | Pt 100mW;BVCEO 10V;ICBO 5.0uA,hfe 60typ;Cob 15p typ;NF 16db;fab 5.0M min |
| 12 | 2N1169 | 2 | N-A | Ge | TO5 | A | Pt 120mW;BVCEO 40V max;VP 20V max;fab 4.5MHz min;hFE 20 min. |
| 13 | 2N1170 | 2 | N-A | Ge | TO5 | A | Pt 120mW;BVCEO 30V;IC 50mA max;fab-40Mc typ. |
| 14 | 2N1640 | 2 | P-Δ | Si | TO5 | A | P-25W max;BVCEO:30V;IC:50mA max;fab-80Mc Typ. |
| 15 | 2N1641 | 2 | P-Δ | Si | TO5 | A | P-25W max;BVCEO:30V;IC:50mA max;fab-1.2Mc Typ. |
| 16 | 2N1642 | 2 | P-Δ | Si | TO5 | A | P-150mW;VEBO:25V max;VCEO:25V max;fab-5.0Mc min. |
| 17 | 2N1891* | 2 | N | Ge | TO5 | A | P-15W max;BVCEO:30V;IC:30A max;ton-1300ns;toff-1800ns;fab-3Mc |
| 18 | 2N1894 | 2 | N-A | Ge | TO5 | A | P-15W max;BVCEO:25V;IC:30A max;ton-1300ns;toff-1800ns;fab-5Mc |
| 19 | 2N1895 | 2 | N-A | Ge | TO5 | A | P-15W max;BVCEO:20V;IC:30A max;ton-1100ns;toff-1800ns;fab-8Mc |
| 20 | 2N1996 | 2 | N-A | Ge | TO5 | A | P-25W max;BVCEO:30V;BVCEO:30V;BVCEO:15V/hFE:15;VO-6mV max. |
| 21 | 2N2474 | 2 | P-Δ | Si | TO5 | A | Pd-150mW max;hFE-15 at 100uA;BVCEO:30V; IC:50mA max. |
| 22 | 2N2968 | 2 | P-PA | Si | TO5 | A | Pd-150mW max;hFE-15 at 100uA;BVCEO:30V; IC:50mA max. |
| 23 | 2N2969 | 2 | P-PA | Si | TO18 | A | Pd-150mW max;hFE-15 at 100uA;BVCEO:30V; IC:50mA max. |
| 24 | 2N2970 | 2 | P-PA | Si | TO5 | A | Pd-150mW max;hFE-10 at 100uA;BVCEO:20V; IC:50mA max. |
| 25 | 2N2971 | 2 | P-PA | Si | TO18 | A | Pd-150mW max;hFE-10 at 100uA;BVCEO:20V; IC:50mA max. |
| 26# | AC130 | 2 | P | Ge | TO5 | A | P-14W max; BVCEO:20V; IC:1A max; fab-2.0Mc. |
| 27 | GT34S | 2 | P | Ge | TO22 | A | P-150mW;BVCEO:40V;VEBO:40V;ICBO:100uA;hfe-15 at 10ma. |
| 28# | 2S155 | 3 | Δ | Si | TO3 | DF | MOS FET;toff 18ns;ton 12ns;tstg 9ns;Coss 700pF;Crss 60pF |
| 29# | 2S156 | 3 | Δ | Si | TO3 | C | Dual Gate VHF Mosfet;toff 18ns;ton 12ns;tstg 9ns;Coss 700pF;Crss 60pF |
| 30# | 3SK47* | 3 | N-MOS | Si | TO72 | DX | Dual Gate Hi-Freq Ampl/Variable Resistor |
| 31 | AD842 | 3 | P | Si | TO72 | PA | Dual Gate;IG 50pAmax;VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 40uV/C |
| 32 | AD3954 | 3 | P | Si | TO71 | PA | Dual Gate;IG 50pAmax;VGS(1-2)10mVmax;ΔVGS(1-2)/ΔT 10uV/C |
| 33 | AD3954A | 3 | P | Si | TO71 | PA | Dual Gate;IG 50pAmax;VGS(1-2)10mVmax;ΔVGS(1-2)/ΔT 5uV/C |
| 34 | AD3955 | 3 | P | Si | TO71 | PA | Dual Gate;IG 50pAmax;VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 25uV/C |
| 35 | AD3956 | 3 | P | Si | TO71 | PA | Dual Gate;IG 50pAmax;VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 50uV/C |
| 36 | AD3958 | 3 | P | Si | TO71 | PA | Dual Gate;IG 50pAmax;VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 100uV/C |
| 37 | BF7-35 | 3 | N | Si | W52c | | VMOS;30-175MHz;Po 7W;Vds 35;EFF 50%;Gain 12db |
| 38 | BF25-35 | 3 | N | Si | W129 | | VMOS;30-175MHz;Po 25W;VDS 35;EFF 50%;Gain 10db min |
| 39 | BF50-35 | 3 | N | Si | W129 | | VMOS;30-175MHz;Po 50W;Vds 35;EFF 50%;Gain 9db min |
| 40 | BF100-35 | 3 | N | Si | | | VMOS;30-175MHz;Po 100W;Vds 35;EFF 50%;min;Gain 8db min |
| 41 | CD643 | 3 | N | Si | TO5 | | Broadband RF Amp;Dual;Matched for Vpo±25mV,gm±5%;Thru 500MHz |
| 42 | CD860 | 3 | N | Si | TO71 | | Ultra Low Noise;Dual;Matched for Vpo±25mV,gm±5%;Max Vpo 3.0V |
| 43 | CM856 | 3 | N | Si | TO46 | | Low Ron Switching;Max Rds(On) 1.0Ω;Idss min 750mA;Vp-10V |
| 44 | HCR1020 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 20V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 45 | HCR1025 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 25V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 46 | HCR1030 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 30V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 47 | HCR1040 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 40V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 48 | HCR1050 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 50V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 49 | HCR1070 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 70V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 50 | HCR1100 | 3 | P | Si | TO3 | FA | High Conduct Rect;Vprv 100V;VF 8V;IF 40A;PT 32W;IR 100mADC |
| 51 | PTC181 | 3 | | Si | TO72 | ES | Dual Gate VHF Mosfet;gfs 8.0m Mhos;VDS 25V;Pd 1.2W;IG 10/10mA Max |
| 52 | PTC182 | 3 | | Si | TO72 | ES | Dual Gate VHF Mosfet;gfs 30m Mhos;VDS 27V;Pd 1.2W IG 10/10mA Max |
| 53 | PTC184 | 3 | | Si | TO72 | ES | Dual Gate VHF Mosfet;gfs 9.0m Mhos;VDS 20V;Pd 360mW;IG 10/10mA Max |
| 54 | SA2345 | 3 | N-PL | Si | TO78 | | BVDG:50W min;IGSS:50nA max;RP:80mohms min;IG:20nA max |
| 55 | SK3187-RT | 3 | N | Si | R176k | DXΔ | Dual;PT 360mW;ID 50mA;VDS 27V;IDS 15mA;VGS 1 and 2 ±6.0V;gfs 25mMho |
| 56 | SK3448-RT | 3 | N | Si | R182e | DA | Junction;PT 150mW;ID 10mA;VDG 30V;IDS 12mA;VGS 1.5V;gfs 3.0mMho |
| 57 | SK3531-RT | 3 | N | Si | R176k | DW | Pt 330mW;VDS 35V;ID 50mA;IDS 15mA;VGS ±10V;gfs 6.0mMho |
| 58 | 2N1019 | 4 | PNN | Ge | Si | | P-10W max;BVCEO:30V; Ic:3.0A max;hFE:15000 Typ;VCE:5.0V;Ic:1.0A. |
| 59 | 2N529 | 5 | N-P | Ge | TO5 | A | BVCEO 15V;Pt 100mW max;fab 2.5MHz;hfe 15-20 |
| 60 | 2N530 | 5 | N-P | Ge | TO5 | A | BVCEO 15V;Pt 100mW max;fab 3.0MHz;hfe 20-25 |
| 61 | 2N531 | 5 | N-P | Ge | TO5 | A | BVCEO 15V;Pt 100mW max;fab 3.5MHz;hfe 25-30 |
| 62 | 2N532 | 5 | N-P | Ge | TO5 | A | BVCEO 15V;Pt 100mW max;fab 4.0MHz;hfe 30-35 |
| 63 | 2N533 | 5 | N-P | Ge | TO5 | A | BVCEO 15V;Pt 100mW max;fab 4.5MHz;hFE 35-40. |
| 64 | 2N2707 | 5 | N | Ge | TO1 | A | Matched pair of 2N2430 and 2N2706; hFE1/2-1.1 max. |
| 65 | 2N3773 | 5 | N | Si | TO3 | CØ | w/2N6609;PT 150W;VCEO 160V;VCEO(sus)140V;hFE 5 min At IC 16A;VCE 4V;VCE(sat).25 max |
| 66 | 2N3838† | 5 | P | Si | TO89 | PB | Pt 35W;BVCEO:60V;hFE:35 min;ft:200Mc min;tr:40ns;trf:90ns. |
| 67 | JAN2N3838† | 5 | P-NØ | Si | X27 | | Pd 350mW both;BVCEO 60V;BEBO 5.0V;BVCEO 40V;ICBO 10nA at VCB 50V |
| 68 | 2N4079 | 5 | PN | Ge | TO1 | A | 2N4077/2N4078;hFE1/hFE2 1.40 max at VCB 0.0 and IE 500mA. |
| 69 | 2N4107 | 5 | P | Ge | TO1 | A | 2N4105/2N4106;hFE1/hFE2 1.25 at VCB 0V;IE:500mA. |
| 70 | 2N4136 | 5 | P | Ge | TO1 | A | Pair of 2N2430 and 2N2431;hFE1/hFE2:1.4 at VCB:0.0V and IE:300mA. |
| 71 | 2N4854† | 5 | A | Si | R138 | PN | Pc 30W each;VC1-2-120V max;BVCEO-60V max;IC:600mA;BVCEO-40V max. |
| 72 | JAN2N4854† | 5 | P-NØ | Si | R52 | PL | Pc 600m both;BVCEO 60V;BEBO 5.0V;BVCEO 40V;ICBO 10n at VCB 50V. |
| 73 | 2N4855† | 5 | P | Si | R138 | PN | Pc 30W each;VC1-2-120V max;BVCEO-60V max;IC:600mA;BVCEO-40V max. |
| 74 | 2N6609 | 5 | P | Si | TO3 | CØ | w/2N3773;PT 150W;VCEO 160V;VCEO(sus)140V;hFE 5 min At IC 16A;VCE 4V;VCE(sat).25 max |
| 75# | 2SB43 | 5 | P-A | Ge | TO1 | | fab-1.0Mc; BVCEO-25V; IC-.05A max; hFE-70 at IC-.05A |
| 76# | 2SD43 | 5 | A | Ge | TO1 | | fab-1.0Mc; BVCEO-25V; IC-.05A max; hFE-70 at IC-.05A |
| 77 | 40396 | 5 | N-P | Ge | TO1 | A | Pt-30W(each);VCEO-18V max;VEBO-2.5V max. |
| 78 | AC127/AC128 | 5 | N-P-A | Ge | TO1 | F | Matched pair of AC127 and AC128;hFE1/hFE2 1.1 at VCB 0.0V,Ic 300mA. |
| 79 | AC127/AC132 | 5 | A | Ge | TO1 | | Matched pair of AC127 and AC132 |
| 80# | AC187/AC188 | 5 | A | Ge | TO1 | A | hFE1/2-.89 min; BVCEO:25V; IC peak-2A. |
| 81# | AD161/AD162 | 5 | A | Ge | F4b | | BVCEO-32V;IC-2.0A;ft-1.0Mc;Pd-3.0W;hFE-40min;hFE1/2-1.25max. |
| 82# | BC635-BC636 | 5 | N-P-PE† | Si | TO92 | B | Pt 1.0W each;hFE1/2 1.3 At IC 150mA,VCE 2.0V;VCEO 45V;VCEO 45V;ICM 1.5A |
| 83# | BC637-BC638 | 5 | N-P-PE† | Si | TO92 | B | Pt 1.0W each;hFE1/2 1.3 At IC 150mA,VCE 2.0V;VCEO 60V;VCEO 60V;ICM 1.5A |
| 84# | BC639-BC640 | 5 | N-P-PE† | Si | TO92 | B | Pt 1.0W each;hFE1/2 1.3 At IC 150mA,VCE 2.0V;VCEO 100V;VCEO 100V;ICM 1.5A |
| 85# | BD135-BD136 | 5 | N-P-PL | Si | B21 | D | Complementary Pairs;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 86# | BD137-BD138 | 5 | N-P-PL | Si | B21 | D | Complementary Pairs;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 87# | BD139-BD140 | 5 | N-P-PL | Si | B21 | D | Complementary Pairs;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 88# | BD201-BD202 | 5 | N-P-E | Si | B23 | | Pt 55W;hFE1/2 1.6 max at IC 1.0A,VCE 2.0V. |
| 89# | BD203-BD204 | 5 | N-P-E | Si | B23 | | Pt 55W;hFE1/2 1.6 max at IC 1.0A,VCE 2.0V. |
| 90# | BD226-BD227 | 5 | N-P-PL | Si | B21 | BØ | Pt 10W;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 91# | BD228-BD229 | 5 | N-P-PL | Si | B21 | BØ | Pt 10W;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 92# | BD230-BD231 | 5 | N-P-PL | Si | B21 | BØ | Pt 10W;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 93# | BD233-BD234 | 5 | N-P-E | Si | B21 | BØ | Pt 25W;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 94# | BD235-BD236 | 5 | N-P-E | Si | B21 | BØ | Pt 25W;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 95# | BD237-BD238 | 5 | N-P-E | Si | B21 | BØ | Pt 25W;hFE1/2 1.6 max at IC 150mA,VCE 2.0V. |
| 96# | BD433-BD434 | 5 | N-P-E | Si | TO126 | BØ | Complementary Pairs;hFE1/2 1.4 max at IC 500mA,VCE 1.0V. |
| 97# | BD435-BD436 | 5 | N-P-E | Si | TO126 | BØ | Complementary Pairs;hFE1/2 1.4 max at IC 500mA,VCE 1.0V. |
| 98# | BD437-BD438 | 5 | N-P-E | Si | TO126 | BØ | Complementary Pairs;hFE1/2 1.8 max at IC 500mA,VCE 1.0V. |
| 99# | BD645/646 | 5 | N-P | Si | | | Complementary Darlingtons;Pt 62.5W;VCEO 80;IC 12A;hfe 1/2 2.5 |
| 100# | BD647/648 | 5 | N-P | Si | | | Complementary Darlingtons;Pt 62.5W;VCEO 100;IC 12A;hfe 1/2 2.5 |
| 101# | BD649/650 | 5 | N-P | Si | | | Complementary Darlingtons;Pt 62.5W;VCEO 100;IC 12A;hfe 1/2 2.5 |
| 102# | BD651/652 | 5 | N-P | Si | | | Complementary Darlingtons;Pt 62.5W;VCEO 120;IC 12A;hfe 1/2 2.5 |
| 103# | BD677/678 | 5 | N-P | Si | TO126 | B | Complementary Darlingtons;Pt 40W;VCEO 60;IC 6A;hfe 1/2 2.5 |
| 104# | BD679/680 | 5 | N-P | Si | TO126 | B | Complementary Darlingtons;Pt 40W;VCEO 80;IC 6A;hfe 1/2 2.5 |
| 105# | BD681/682 | 5 | N-P | Si | TO126 | B | Complementary Darlingtons;Pt 40W;VCEO 100;IC 6A;hfe 1/2 2.5 |
| 106# | BD683/684 | 5 | N-P | Si | TO126 | B | Complementary Darlingtons;Pt 40W;VCEO 120;IC 6A;hfe 1/2 2.5 |
| 107# | BDX62/63 | 5 | N-P | Si | TO3 | CØ | Darlington;Pt 90W;BVCEO 60V;BVCEO 60V;hFE1/hFE2 2.5 max. |
| 108# | BDX62A/63A | 5 | N-P | Si | TO3 | CØ | Darlington;Pt 90W;BVCEO 80V;BVCEO 80V;hFE1/hFE2 2.5 max. |
| 109# | BDX62B/63B | 5 | N-P | Si | TO3 | | Darlington;Pt 90W;BVCEO 100V;BVCEO 100V;hFE1/hFE2 2.5 max |
| 110# | BDX64/65 | 5 | N-P | Si | TO3 | CØ | Darlington;Pt 117W;BVCEO 60V;BVCEO 60V;hFE1/hFE2 2.5 max. |